

Timothy Cockerill

List of Publications by Year in descending order

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26
papers

3,167
citations

758635

12
h-index

580395

25
g-index

26
all docs

26
docs citations

26
times ranked

5142
citing authors

#	ARTICLE	IF	CITATIONS
1	XSEDE: Accelerating Scientific Discovery. Computing in Science and Engineering, 2014, 16, 62-74.	1.2	2,790
2	A distributed feedback ridge waveguide quantum well heterostructure laser. IEEE Photonics Technology Letters, 1991, 3, 6-8.	1.3	66
3	Kinetics of thermal oxidation of AlAs in water vapor. Applied Physics Letters, 1996, 68, 1898-1900.	1.5	55
4	Strained-layer InGaAs-GaAs-AlGaAs buried-heterostructure quantum-well lasers by three-step selective-area metalorganic chemical vapor deposition. IEEE Journal of Quantum Electronics, 1994, 30, 441-445.	1.0	32
5	Submilliampere threshold buried-heterostructure InGaAs/GaAs single quantum well lasers grown by selective-area epitaxy. IEEE Photonics Technology Letters, 1994, 6, 1073-1075.	1.3	23
6	Wavelength tuning in strained layer InGaAs-GaAs-AlGaAs quantum well lasers by selective-area MOCVD. Journal of Electronic Materials, 1994, 23, 115-119.	1.0	21
7	Depressed index cladding graded barrier separate confinement single quantum well heterostructure laser. Applied Physics Letters, 1991, 59, 2694-2696.	1.5	19
8	A strained-layer InGaAs-GaAs-AlGaAs single quantum well broad spectrum LED by selective-area metalorganic chemical vapor deposition. IEEE Photonics Technology Letters, 1994, 6, 1289-1292.	1.3	19
9	Monolithic integration of a strained-layer InGaAs-GaAs-AlGaAs quantum-well laser with a passive waveguide by selective-area MOCVD. IEEE Photonics Technology Letters, 1993, 5, 448-450.	1.3	18
10	Characterization of an InGaAs-GaAs-AlGaAs strained-layer distributed-feedback ridge-waveguide quantum-well heterostructure laser. IEEE Photonics Technology Letters, 1992, 4, 296-299.	1.3	17
11	Differential gain in bulk and quantum well diode lasers. IEEE Photonics Technology Letters, 1991, 3, 1057-1060.	1.3	15
12	Electroabsorption properties of a single GaAs quantum well. Physical Review B, 1991, 44, 13478-13486.	1.1	15
13	Scatter loss in disorder-delineated GaAs heterostructure laser waveguides with native and blue shifted active regions. Applied Physics Letters, 1990, 57, 741-743.	1.5	12
14	Distributed feedback strained layer quantum well heterostructure 980 nm laser fabricated by two-step metalorganic chemical vapor deposition. Applied Physics Letters, 1993, 62, 820-822.	1.5	12
15	Dual-channel strained-layer in GaAs-GaAs-AlGaAs WDM source with integrated coupler by selective-area MOCVD. IEEE Photonics Technology Letters, 1994, 6, 1167-1169.	1.3	10
16	Nonplanar quantum well heterostructure window laser. Applied Physics Letters, 1989, 54, 1634-1636.	1.5	8
17	Low drive voltage GaAs quantum well electroabsorption modulators obtained with a displaced junction. IEEE Photonics Technology Letters, 1994, 6, 619-622.	1.3	7
18	Loss in heterostructure waveguide bends formed on a patterned substrate. IEEE Photonics Technology Letters, 1989, 1, 120-122.	1.3	6

#	ARTICLE	IF	CITATIONS
19	Characterization of electrical and optical loss of MOCVD regrowth in strained layer InGaAs-GaAs quantum well heterostructure lasers. <i>Journal of Crystal Growth</i> , 1992, 124, 553-557.	0.7	6
20	Characteristics of step-graded separate confinement quantum well lasers with direct and indirect barriers. <i>Journal of Applied Physics</i> , 1990, 68, 1964-1967.	1.1	5
21	Modal properties of depressed cladding semiconductor waveguides and lasers. <i>IEEE Journal of Quantum Electronics</i> , 1994, 30, 2817-2826.	1.0	5
22	High-power pulsed operation of an optimized nonplanar corrugated substrate periodic laser diode array. <i>IEEE Journal of Quantum Electronics</i> , 1990, 26, 222-224.	1.0	3
23	Multiple quantum well mixing and index-guided quantum well heterostructure lasers by MeV ion implantation. <i>Optical and Quantum Electronics</i> , 1991, 23, S967-S974.	1.5	1
24	Isolated electronic impurity-induced disordering: $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}/\text{In}$. <i>Applied Physics Letters</i> , 1991, 59, 2880-2882.	1.5	1
25	Phase-locked ridge waveguide InGaAs/GaAs/AlGaAs strained-layer quantum well heterostructure laser arrays. <i>Applied Physics Letters</i> , 1991, 59, 3222-3224.	1.5	1
26	In-phase operation of high-power nonplanar periodic laser arrays. <i>Applied Physics Letters</i> , 1991, 58, 113-115.	1.5	0